Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Electronic Supplementary Information for

Straintronics in Two-Dimensional in-Plane Heterostructures of Transition-Metal Dichalcogenides

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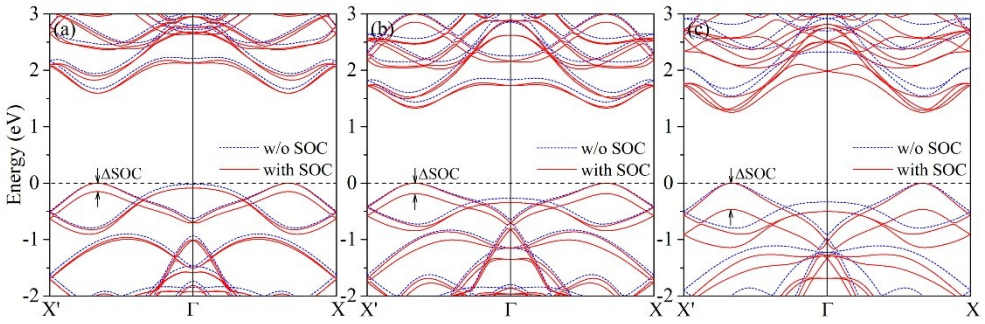

Figure S1: Band structures for MoS_2, $MoSe_2$ and WSe_2 with SOC effects taken into account, the Fermi level is set to zero.

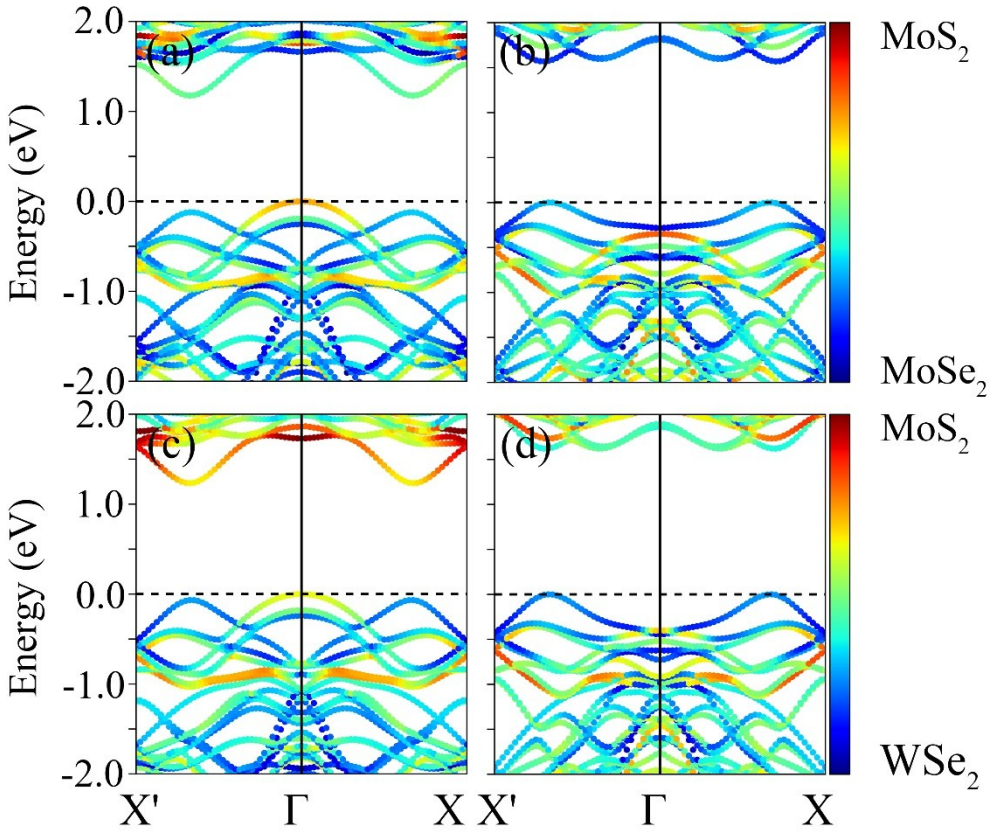

Figure S2 Band structures for $MoSe_2/MoS_2$, $MoS_2/MoSe_2$, WSe_2/MoS_2 and MoS_2/WSe_2 with superlattice models and without local structure relaxation, the Fermi level is set to zero.

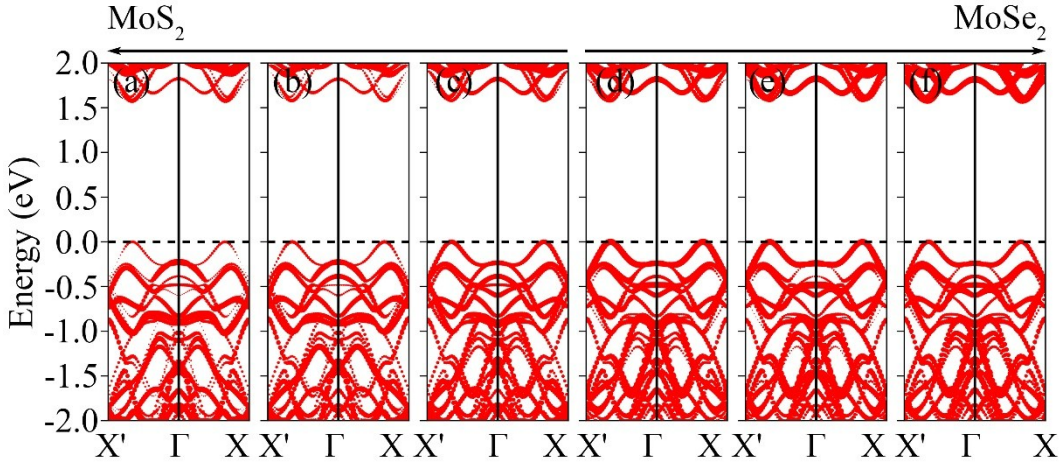

Figure S3 Projected band structure for $MoS_2/MoSe_2$, the Fermi level is set to zero.

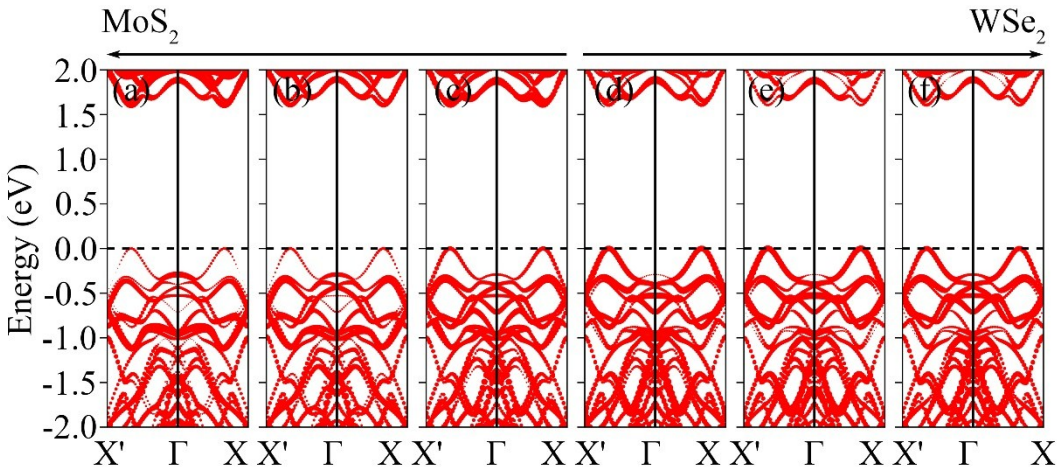

Figure S4 Projected band structure for MoS_2/WSe_2, the Fermi level is set to zero.

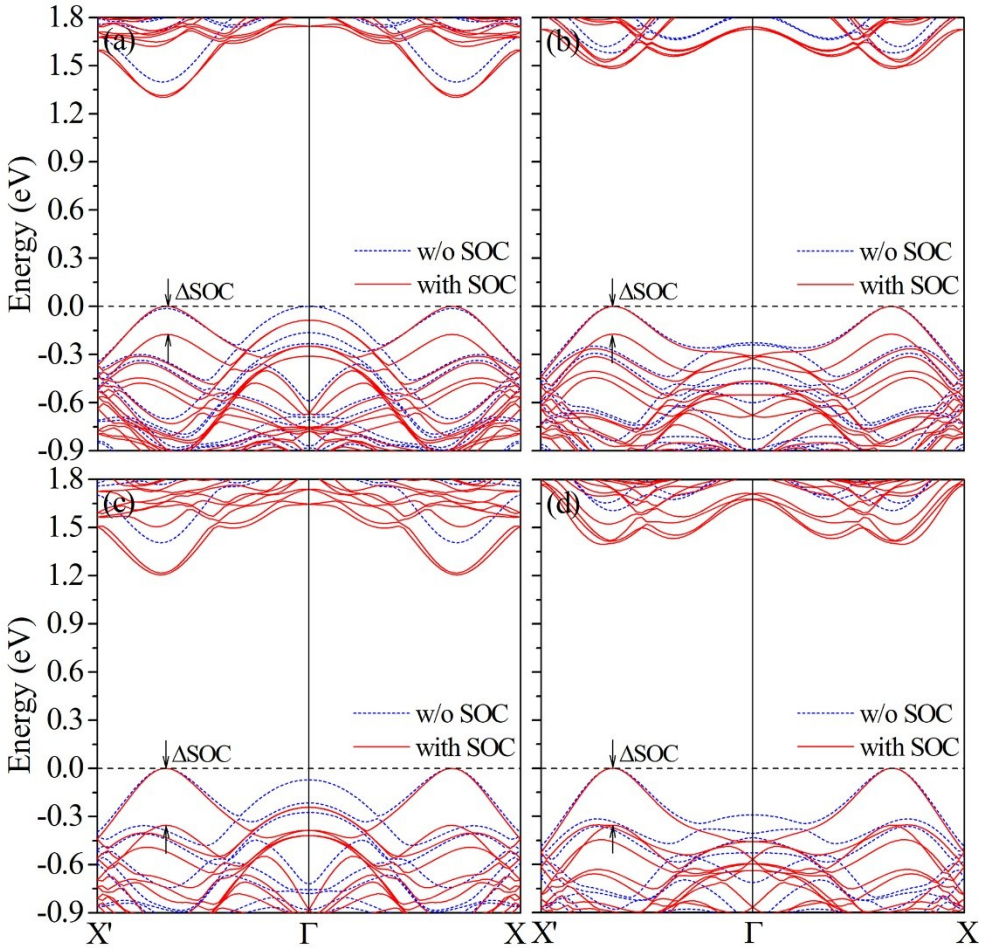

Figure S5 Band structures with the SOC effects taken into account for $MoSe_2/MoS_2$, $MoS_2/MoSe_2$, WSe_2/MoS_2 and MoS_2/WSe_2, the Fermi level is set to zero.

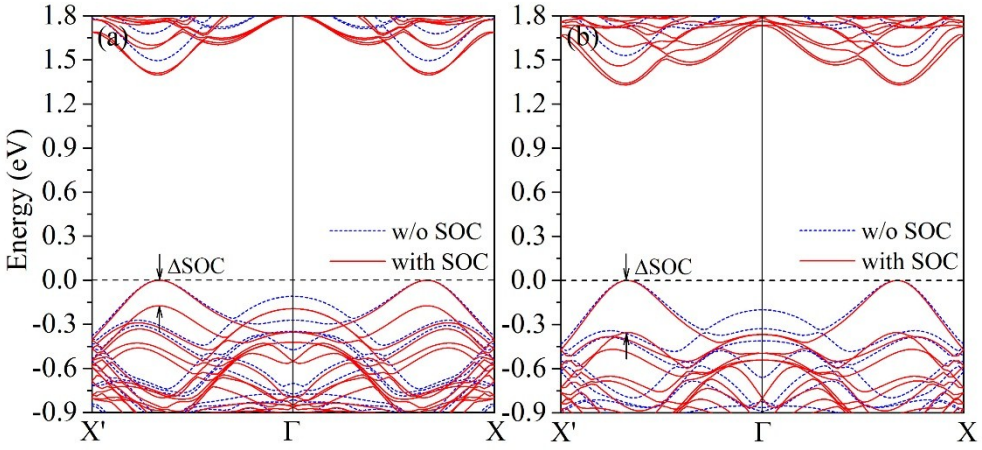

Figure S6 Band structures for $MoSe_2/MoS_2$-a and WSe_2/MoS_2-a with the SOC effects taken into account, the Fermi level is set to zero.